## Comment on "Microscopic Identification and Electronic Structure of a Di-Hydrogen–Vacancy Complex in Silicon by Optical Detection of Magnetic Resonance"

In a Letter, Chen *et al*, [1] reported the observation of a dihydrogen-vacancy complex in silicon (VH<sub>2</sub>) by ODMR (optical detection of magnetic resonance). A careful look at the spin-Hamiltonian parameters indicates that they coincide with those of the excited state (S = 1) Si-*SL*1 spectrum of the monovacancy-oxygen center, OV\* [2,3], also known as the *A* center (see Table I, Fig. 1). Clearly, this raises some questions as to the validity of the identification of the spectrum of Chen *et al.* to VH<sub>2</sub>.

However, the similarity could still be accidental. To check whether the spectra are different or are indeed one and the same, we have recreated the spectrum of Chen *et al.* by proton and deuteron implantation into float-zone and Czochralski (oxygen-rich) silicon. We found that the signal was 2 orders of magnitude more intense in the Czochralski material, and therefore conclude that it is oxygen related, as expected in the model of  $OV^*$ . In view of this, the choice of Czochralski silicon for the experiments of Chen *et al.* was unfortunate.

The identification of the spectrum to VH<sub>2</sub> by Chen et al. was based on a difference between linewidths of the resonances in proton- and deuteron-implanted silicon. This broadening was assigned to an unresolved hyperfine (HF) interaction with two equivalent hydrogen nuclei. Unfortunately, the linewidth in ODMR is very large ( $\approx 0.3$  mT). In conventional EPR (electron paramagnetic resonance) the resonances have a much smaller linewidth (0.09 mT), and the seemingly 1:2:1 splitting assigned to HF interaction with two hydrogen nuclei is resolved into a 1:6.8:1 splitting (see Fig. 2) caused by the hyperfine interaction with a shell of six equivalent silicon atoms. In the model of OV\* these are the six second-shell atoms that are bonded to the two first-shell atoms accommodating the two paramagnetic electrons in dangling bonds. Note that the latter HF interaction with the first-shell silicon atoms is already well resolved by ODMR. The difference of the resonances of the Si:D and Si:H samples as observed

TABLE I. Spin-Hamiltonian parameters according to Chen et al. [1] and Brower [2]. The spectra have orthorhombic-I  $(C_{2v})$  symmetry and S = 1.  $H = \mu_B \mathbf{B} \cdot g \cdot \mathbf{S} \cdot D \cdot \mathbf{S} + \mathbf{S} \cdot A_{Si} \cdot \mathbf{I}$ .

Chen et al.	[100]	[011]	[011]	
g	$\bar{2}.00\bar{2}$	2.005	2.002	
D	-348	-302	650	MHz
$A_{\rm Si}$	$A_{\parallel} = 200, A_{\perp} 114$			MHz
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Brower	[100]	[011]	[011]	
g	2.0076	2.0102	2.00577	
D	-350	-307	657	MHz
$A_{\rm Si}$	$A_{\parallel} = 216, A_{\perp} = 112$			MHz



FIG. 1. Comparison of the angular dependences of the spectrum simulated with the Hamiltonian of Table I (without Si-HF) with the parameters given by Chen *et al.* (dashed) and Brower (solid).

by Chen *et al.*, i.e., the apparent enhancement of the hyperfine lines, is possibly due to saturation effects; hyperfine lines can saturate at a later stage. The resonance shown in Fig. 3(b) of Ref. [1] (Si:D) could be less saturated and the line shape more closely reflecting the 4.7% abundance of silicon.

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FIG. 2. Details showing a fine structure resonance with the first (1st) and second (2nd) shell  $^{29}$ Si-HF satellites.